

Masachika Toguchi

List of Publications by Year in descending order

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9
papers

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1478505

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1588992

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72
citing authors

#	ARTICLE	IF	CITATIONS
1	Self-terminating contactless photo-electrochemical (CL-PEC) etching for fabricating highly uniform recessed-gate AlGaIn/GaN high-electron-mobility transistors (HEMTs). Journal of Applied Physics, 2021, 130, .	2.5	4
2	Fabrication of porous gallium nitride (GaN) utilizing two-step etching method and control of its optical properties. Denki Kagaku, 2021, 89, 365-369.	0.0	0
3	Self-termination of contactless photo-electrochemical (PEC) etching on aluminum gallium nitride/gallium nitride heterostructures. Applied Physics Express, 2020, 13, 026508.	2.4	13
4	Thermal-assisted contactless photoelectrochemical etching for GaN. Applied Physics Express, 2020, 13, 046501.	2.4	6
5	Electrodeless photo-assisted electrochemical etching of GaN using a H ₃ PO ₄ -based solution containing S ₂ O ₈ ²⁻ ions. Applied Physics Express, 2019, 12, 066504.	2.4	14
6	Low-Damage Etching for AlGaIn/GaN HEMTs Using Photo-Electrochemical Reactions. IEEE Transactions on Semiconductor Manufacturing, 2019, 32, 483-488.	1.7	6
7	Photoelectrochemical Etching Technology for Gallium Nitride Power and RF Devices. IEEE Transactions on Semiconductor Manufacturing, 2019, 32, 489-495.	1.7	6
8	Simple wet-etching technology for GaN using an electrodeless photo-assisted electrochemical reaction with a luminous array film as the UV source. Applied Physics Express, 2019, 12, 031003.	2.4	21
9	Effects of a photo-assisted electrochemical etching process removing dry-etching damage in GaN. Japanese Journal of Applied Physics, 2018, 57, 121001.	1.5	25